

Citations for Ion : **Be**

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1959	Vorob'Ev, Yu. A. 'Range of Nitrogen and Beryllium Ions in Air' <i>Zh. Eksp. Teor. Fiz.</i> , 35, 1306-07 (1958). [Engl. Trans. Sov. Phys. JETP, 8, 912 (1959)] Comment : R. 4.9-9.5 MeV N, 3.1, 3.7 MeV Be -> Air	1959-Voro
1960	Schambra, P. E. Rauth, A. M. Northcliffe, L. C. 'Energy Loss Measurements for Heavy Ions in Mylar and Polyethylene' <i>Phys. Rev.</i> , 120, 1758 (1960) Comment : S. He, B, Be, C, N, O, F, Ne (10 MeV/amu) -> Mylar, Polyethylene	1960-Scha2
1962	Hower, C. O. Fairhall, A. W. 'Ranges of Be ⁹ Ions in Gold and Aluminum' <i>Phys. Rev.</i> , 128, 1163-65 (1962) Comment : R. 2-29 MeV ⁹ Be -> Al, Au.	1962-Howe
1962	Teplova, Ya. A. Nikolaev, V. S. Dimitriev, I. S. Fateeva, L. N. 'Slowing Down of Multicharged Ions in Solids and Gases' <i>Zh. Eksp. Teor. Fiz.</i> , 42, 44-60 (1962)[Engl. Trans. Sov. Phys., JETP15, 31-41 (1962)] Comment : S, R.(75-1500 keV/amu) He, Li, Be, B, C, N, O, Ne, Na, Mg, Al, P, Cl, K, Br, Kr -> H ₂ , He, CH ₄ , Benzene, Air, Ar, S. Same -> Al, Ni, Ag, Au	1962-Tepl
1963	Ormrod, J. H. Duckworth, H. E. 'Stopping Cross Sections in Carbon for Low-Energy Atoms with Z < 12' <i>Can. J. Phys.</i> , 41, 1424-42 (1963) Comment : S. (10-130 keV) H, He, Li, Be, B, C, N, O, F, Ne, Na, Mg -> C	1963-Ormr
1968	Chu, W. K. Bourland, P. D. Wang, K. H. Powers, D. 'Range and dE/dx of C, N, O, F, and Ne in Be and C from 500 keV to 2 MeV' <i>Phys. Rev.</i> , 175, 342-53 (1968) Comment : S,R. (0.2-2.0) MeV C, N, O, F, Be; 0.2-1.5 MeV O -> C, 0.5-2.0 MeV Ne -> Be, C	1968-Chu
1969	Macdonald, J. R. Sidenius, G. 'The Total Ionization in Methane of Ions with 1 <= Z1 <= 20 at Energies from 10 to 120 keV' <i>Phys. Letters A</i> , 28, 543-44 (1969) Comment : S. 10-120 keV H, He, Li, Be, B, C, N, O, F, Ne, Na, Mg, Al, Si, P, S, Cl, Ar, Ca, V, Sc, Ti -> CH ₄	1969-Macd
1971	Hvelplund, P. 'Energy Loss and Straggling of 100-500 keV Atoms with 2 <= Z1 <= 12 in Various Gases' <i>Kgl. Danske Videnskab. Selskab Mat. Fys. Medd.</i> , 38, No. 4, P. 1-25 (1971) Comment : S,dS. (100-500 keV) He, Li, Be, B, C, N, O, F, Ne, Na, Mg -> Air, He, Ne, H ₂ , O ₂	1971-Hvel
1974	Sidenius, G. 'Systematic Stopping Cross Section Measurements with Low Energy Ions in Gases' <i>Kgl. Danske Videnskab. Selskab. Mat. Fys. Medd.</i> , 39, No. 4, 1-32 (1974) Comment : S. 0.6-70 keV H, He, 2-120 keV ⁶ Li, ⁷ Li, 3-120 keV Be, B, C, N, O, F, Ne -> CH ₄	1974-Side

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1976	Comas, J. Plew, L. 'Beryllium and Sulfur Ion-Implanted Profiles in GaAs' <i>J. Elec. Mater.</i> , 5, 209-221 (1976) <i>Comment</i> : R. 100, 200 keV Be, S -> GaAs	1976-Coma
1976	Comas, J. Plew, L. Chatterjee, P. K. Mclevige, W. V. Vaidyanathan, K. V. 'Impurity Distribution of Ion-Implanted Be in GaAs by Sims, Photoluminescence, and Electrical Profiling' <i>Ion Implantation in Semiconductors, Ed. by F. Chernow, J. A. Borders, D. K. Brice, 141-148 (1976)</i> <i>Comment</i> : R. 250 keV Be -> GaAs	1976-Coma2
1976	Dietrich, H. B. Comas, J. 'Anomalous Redistribution of Ion-Implanted Dopants' <i>Ion Implantation in Semiconductors, Ed. by F. Chernow, J. A. Borders, D. K. Brice, 735-742 (1976)</i> <i>Comment</i> : R. 60 keV Al -> Si, 100 keV Be -> Si, GaAs	1976-Diet
1976	Hartemann, P. Marizot, M. 'Ion Implantation in Piezoelectric Substrates' <i>Ion Implantation in Semiconductors, Ed. by F. Chernow, J. A. Borders, D. K. Brice, 257-264 (1976)</i> <i>Comment</i> : R. 100 keV He, Li, Be -> Piezoelectric Substrates	1976-Hart
1976	Hoffman, I. Jager, E. Muller-Jahreis, U. 'Z1-Dependence of Electronic Energy Stragglng of Light Ions' <i>Rad. Effects</i> , 31, 57 (1976) <i>Comment</i> : dS. 2 <= Z1 <= 10 (10-100 Kev) -> C, Si	1976-Hoff
1976	Santry, D. C. Werner, R. D. 'Range of Heavy Ions Implanted into Solids as Measured by He Ion Backscattering' <i>Nucl. Inst. Methods</i> , 139, 135-146 (1976) <i>Comment</i> : R, dR. 0.12-2.0 MeV Bi, Xe, Kr -> C, Al, Si	1976-Sant
1977	Datz, S. DelCampo, J. G. Dittner, P. F. Miller, P. D. Biggerstaff, J. A. 'Higher-Order Z1 Effects and Effects of Screening by Bound K-Electrons on the Electronic Stopping of Channeled Ions' <i>Phys. Rev. Letters</i> , 38, 1145-1148 (1977) <i>Comment</i> : S. 2 MeV/amu H, He, Li, Be, B, C, N, O, F, 3.5 MeV/amu H, He, Li, Be, B -> Au [111]	1977-Datz
1977	Datz, S. Gomez del Campo, J. Dittner, P. F. Miller, P. D. Biggerstaff, J. A. 'Higher Order Z1 Effects and Effects of Screening by Bound k-electrons on the Electronic Stopping of Channeled Ions' <i>Phys. Rev. Letters</i> , 38, 1145-1148 (1977) <i>Comment</i> : S. H, He, Li, Be, B (3.5 MeV/amu) -> Au Channeled stopping powers.	1977-Datz2

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Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1977	Mertens, P. 'Energy Loss of Light 100 - 300 keV Ions in Thin Metal Foils' <i>Nucl. Inst. Methods, 149, 149-153 (1978)</i> <i>Comment : S, dS.H, He, Li, Be, B, C, N, O, F, Ne (300 keV) -> C, Ni, Co, Nb. 300 keV He, Ne, F, O, N -> C, Al, Ti, Mn, Fe, Co, Ni, Cu, Nb, Ag, Au</i>	1977-Mert
1978	Ullrich, B. M. Mayer, J. W. 'Stragglng of MeV Ions in Osmium' <i>Boehm. Phys. Gess. J., 1, 478-489 (1978)</i> <i>Comment : S, dS. 2-50 MeV H, He, Li, Be, B, C, N, O -> Os</i>	1978-Ullr
1979	Comas, J. Wilson, R. G. 'Channeling and Random Equivalent Depth Distributions of 150 keV Li, Be, and B Implanted in Si' <i>Preprint (1979) 2</i> <i>Comment : S, R, dR. 150 keV Li, Be, B -> Si</i>	1979-Coma
1979	Donnelly, J. P. Armiento, C. A. 'Beryllium-Ion Implantation in InP and In(1-X)Ga(X)As(Y)P(1-Y)' <i>Appl. Phys. Letters, 34, 96-99 (1979)</i> <i>Comment : R. 50-400 keV Be -> InP, InGaAsP</i>	1979-Donn
1980	Mertens, P. Krist, Th. 'Stopping Ratios of 50-300 keV Light Ions in Metals' <i>Nucl. Inst. Methods, 168, 33-39 (1980)</i> <i>Comment : S, dS. 30-300 keV H, He, Li, Be -> C, Al, Cu, Ag, Au</i>	1980-Mert
1980	Sofield, C. J. Cowern, N. E. B. Freeman, J. M. 'Charge-Exchange Effects in Energy-Loss Stragglng' <i>Nucl. Inst. Methods, 170, 221-225 (1980)</i> <i>Comment : R, dR. 0-50 MeV Atomic Numbers 1-16 -> Al</i>	1980-Sofi
1980	Wilson, R. G. Comas, J. 'Correlation of Atomic Distribution and Implantation Induced Damage Profiles in Be-Ion Implanted Si' <i>Rad. Effects, 47, 137-142 (1980)</i> <i>Comment : R, dR. 300 keV Be -> Si</i>	1980-Wils
1982	Mertens, P. Krist, Th. 'Stopping Ratios of 50 - 300 keV Light Ions in Metals' <i>Nucl. Inst. Methods, 194, 57 (1982)</i> <i>Comment : S. 50-300 keV H, He, Li, Be -> C, Al, Cu, Ag, Au</i>	1982-Mert
1982	Mertens, P. Krist, Th. 'Stopping Ratios for 30 - 300 keV Ions with $1 \leq Z \leq 5$ ' <i>J. Appl. Phys., 53 (11), 7343 - 7349 (1982)</i> <i>Comment : S. H, He, Li, Be, B (30-330 keV) -> C, V, Cr, Fe, Ni, Zn</i>	1982-Mert3

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1984	Adesida, I. Karapiperis, L. 'The Range of Light Ions in Polymeric Resists' <i>J. Appl. Phys.</i> , 56 (6), 1801-1807 (1984) <i>Comment</i> : R, dR. H, He, Li, Be, B, C (5-300 keV) -> PMMA photoresist	1984-Ades
1984	Krist, Th. Mertens, P. 'Application of Brandt's Effective Charge Theory to Measurements for 50-350 keV Ions with $1 \leq Z_1 \leq 5$ ' <i>Nucl. Inst. Methods, B2</i> , 119-122 (1984) <i>Comment</i> : S, H, He, Li, Be, B (50-350 keV) -> C, Al, V, Cr, Fe, Ni, Cu, Zn, Ag, Pt, Au, Bi	1984-Kris
1988	Wilson, R. G. '(111) Random and (110) Channeling Implantation Profiles and Range Parameters in HgCdTe' <i>J. Appl. Phys.</i> , 63 , 5302-5311 (1988) <i>Comment</i> : R, dR. 45 Ions (H to Ta) at 100-700 keV -> HgCdTe	1988-Wils
1988	Wilson, R. G. 'Ion Implantation and SIMS Profiling of Impurities in II-VI Materials HgCdTe and CdTe' <i>J. Crystal Growth</i> , 86 , 735-743 (1988) <i>Comment</i> : R, dR. 52 Ions (H-Hg) at 100-700 keV -> CdTe, HgCdTe	1988-Wils2
1994	Raisanen, J. Rauhala, E. Fulop, Z. Kiss, A. Z. Somorjai, E. 'Stopping Powers of CR-39 Nuclear Track Material for Z=1-14 Ions with 0.25-2.8 MeV/amu' <i>Rad. Meas. (UK)</i> , 23 , 749-752 (1994) <i>Comment</i> : S. Z=1-14 (0.25-2.8 MeV/amu) -> CR-39	1994-Rais2
1996	Misdaq, M. A. Ellassali, R. 'Average Stopping Powers for Channeled Ions using Calculational and Experimental Methods' <i>Nucl. Inst. Methods</i> , 119 , 325-330 (1996) <i>Comment</i> : S. Light ions -> Si, GaAs (channeled)	1996-Misd
1999	Angulo, C. Delbar, T. Graulich, J. S. Leleus, P. 'Stopping Power Measurements: Implications in Nuclear Astrophysics' <i>AIP Conf. Proc.</i> , 495 , 381-384 (1999) <i>Comment</i> : S. Be, B, C, N, O, F, Ne (1 MeV/u) -> C, Al, Ni, CH ₂ , PVC	1999-Angu
2000	Angulo, C. Delbar, Th. Graulich, J. -S. Leleux, P. 'Stopping Powers of Ions at 1 MeV per Nucleon' <i>Nucl. Instl. Methods</i> , V170 , 21-27 (2000) <i>Comment</i> : S. Be, B, C, N, O, F, Ne (1 MeV/u) -> C, Al, Ni, CH ₂ , PVC	2000-Angu

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2001	Zhang, Y. Possnert, G. Whitlow, H. J. 'Measurements of the Mean Energy-Loss of Swift Heavy Ions in Carbon with High Precision' <i>Nucl. Inst. Methods, B183, 34-37 (2001)</i> <i>Comment : S. Li, Be, B, C, N, O, F, Na, Mg, Al, Si, Cr, Mn, Fe (100 - 800 keV/u) -> C</i>	2001-Zhan
2002	Whitlow, H. J. Timmers, H. Elliman, R. G. Weijers, T. D. Zhang, Y. 'Measurement and Uncertainties of Energy Loss in Silicon over a Wide Z1 Range using Time-of-Flight Detector Telescopes' <i>Nucl. Inst. Methods, B195, 133-146 (2002)</i> <i>Comment : S. Li, Be, B, C, N, O, F, Na, Mg, Al, Si, P, Mn, Fe -> Si</i>	2002-Whit2
2002	Zhang, Y. 'High-Precision Measurement of Electronic Stopping Powers for Heavy Ions using High-Resolution Time-of-Flight Spectrometry' <i>Nucl. Inst. Methods, B196, 1-15 (2002)</i> <i>Comment : S. Stopping of 18 Heavy Ions into C, Al and Au Targets</i>	2002-Zhan
2002	Zhang, Y. Possnert, G. 'Electronic Stopping Power of Swift Heavy Ions in Carbon' <i>Nucl. Inst. Methods, B190, 69-73(2002)</i> <i>Comment : S. He, Be, C and Al -> C</i>	2002-Zhan2
2004	Araujo, L.L. Mehar, M. Grande, P.L. Dias, J.F. 'Random Energy Loss and Straggling Study of 9-Be Ions in Silicon' <i>Nucl. Inst. Methods, B219-220, 246-250 (2004)</i> <i>Comment : S. dS. Be -> Si</i>	2004-Arau
2004	Janson, M.S. Linnarsson, M.K. Hallen, A. Svensson, B.G. 'Electronic stopping cross sections in silicon carbide for low-velocity ions with $1 \leq Z1 \leq 15$ ' <i>J. Appl. Phys. 96, 164 (2004)</i> <i>Comment : S. H - P (1.5-300 keV) -> SiC</i>	2004-Jans
2004	Zhang, Yanweb Weber, W. J. 'Electronic stopping powers in silicon carbide' <i>Phys.Rev. B69, 205201 (2003)</i> <i>Comment : S. Be - Au (0.05 - 0.4 MeV/n) -> SiC</i>	2004-Zha2
2004	Zhang, Y. Weber, W. Whitlow, H. J. 'Electronic Stopping Powers for Heavy Ions in Silicon' <i>Nucl. Inst. Methods, B215, 48-56 (2004)</i> <i>Comment : S. 14 light ions (Be-Cu) -> Si</i>	2004-Zha3
2005	Zhang, Yanwen Weber, W. J. Raxpet, A. Possnert, G. 'Electronic stopping powers for He, Be and F ions in Au' <i>Nucl. Instrum. Methods B227,479 (2005)</i> <i>Comment : S. Be, F (0.1 - 0.6 MeV/n) -> Au</i>	2005-Zha1

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2005	Zhang, Yanwen Weber, W. J. McCready, D.E. Grove, D.A. Jensen, J. 'Experimental determination of electronic stopping for ions in silicon dioxide' <i>Appl. Phys. Lett.</i> 87 , 104103 (2005) <i>Comment</i> : S. Be - Si (0.05 - 1.3 MeV/n) -> SiO2	2005-Zha2
2006	Zhang, Yanwen Weber, W. J. Razpet, A. Possnert, G. 'Electronic stopping powers for Be, Ca and Ti in SiC' <i>Nucl. Instrum. Methods B242,82</i> (2006) <i>Comment</i> : S. Be, Ca, Ti (0.05 - 0.2 MeV/n) -> SiC	2006-Zha1
2006	Zhang, Yanwen Weber, W. J. Grove, D. A. Jensen, J. Possnert, G. 'Electronic stopping powers for heavy ions in niobium and tantalum pentoxides ' <i>Nucl.Instrum.Methods B250, 62</i> (2006) <i>Comment</i> : S. Li, Be, O (0.1-1.6 MeV/n) -> Nb2O5, Ta2O5	2006-Zha3
2007	Zadro, M. DiPietro, A. Figuera, P. Fisichella, M. Lattuada, M. 'Stopping Power of Helium Gas for 9-Be Ions from 2 to 31 MeV' <i>Nucl. Inst. Methods, B259, 836-840</i> (2007) <i>Comment</i> : S. Be -> He (gas)	2007-Zadr
2009	Cantero, E.D. Fadanelli, R.C. Montanari, C.C. Behar, M. Eckardt, J.C. 'Experimental and theoretical study of the energy loss of Be and B ions in Zn' <i>Phys. Rev. A79, 042904</i> (2009) <i>Comment</i> : S. Be (52-1090 keV/u), B(45-902 keV/u) -> Zn	2009-CanA
2009	Zhang, Y. Weber, W.J. 'Response of materials to single ion events' <i>Nucl.Instrum.Methods Phys. Res. B267, 1705</i> (2009) <i>Comment</i> : S. He (125-720 keV/n), Be (90-1600 keV/n), O (60-1300 keV/n), F (65-1130 keV/n) -> ZrO2	2009-Zhan